

Youngjae Kim

List of Publications by Year in descending order

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15
docs citations

15
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585
citing authors

#	ARTICLE	IF	CITATIONS
1	Rough-Surface-Enabled Capacitive Pressure Sensors with 3D Touch Capability. <i>Small</i> , 2017, 13, 1700368.	10.0	142
2	Probing the upper band gap of atomic rhenium disulfide layers. <i>Light: Science and Applications</i> , 2018, 7, 98.	16.6	24
3	Anomalous Electron Dynamics Induced through the Valley Magnetic Domain: A Pathway to Valleytronic Current Processing. <i>Nano Letters</i> , 2019, 19, 4166-4173.	9.1	9
4	Tip-Induced Molecule Anchoring in Ni-Phthalocyanine on Au(111) Substrate. <i>Journal of Physical Chemistry C</i> , 2015, 119, 27721-27726.	3.1	8
5	Dual Resonant Sum Frequency Generations from Two-Dimensional Materials. <i>Nano Letters</i> , 2020, 20, 4530-4536.	9.1	8
6	Van der Waals Heterostructure of Hexagonal Boron Nitride with an AlGaIn/GaN Epitaxial Wafer for High-Performance Radio Frequency Applications. <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 59440-59449.	8.0	8
7	Topological band-order transition and quantum spin Hall edge engineering in functionalized X-Bi(111) (X = Ga, In, and Tl) bilayer. <i>Scientific Reports</i> , 2016, 6, 33395.	3.3	7
8	Model for petahertz optical memory based on a manipulation of the optical-field-induced current in dielectrics. <i>New Journal of Physics</i> , 2018, 20, 093029.	2.9	7
9	Effect of crystallinity on the resistive switching behavior of HfAlO _x films. <i>Journal of the Korean Physical Society</i> , 2014, 64, 419-423.	0.7	6
10	Effect of aliovalent impurities on the resistance switching characteristics of sputtered hafnium oxide films. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2015, 33, 032204.	1.2	5
11	Time-resolved photoemission of infinitely periodic atomic arrangements: correlation-dressed excited states of solids. <i>Npj Computational Materials</i> , 2020, 6, .	8.7	5
12	Effect of chemical bonding states in TaO _x base layers on rectifying bipolar resistive switching characteristics. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013, 31, 032206.	1.2	3
13	Electrical Control of the Valley Magnetic Domain and Anomalous Electron Transport in Bilayer MoS_2 Physical Review Applied, 2021, 15, .	3.8	3
14	Ultrafast dynamics of phase and topology in Dirac semiconductors. <i>Materials Today Physics</i> , 2021, 21, 100525.	6.0	2